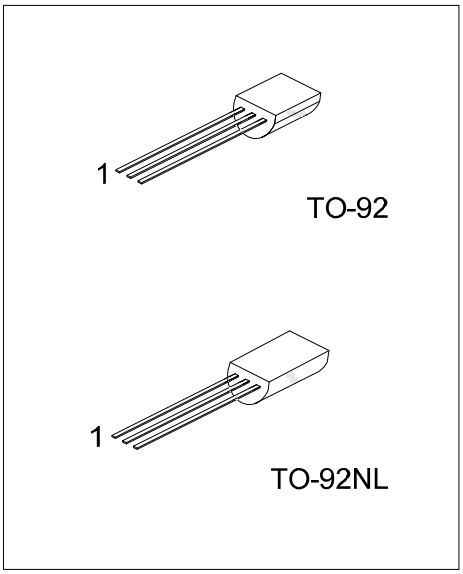
2SC2328A

NPN EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPLIFIER



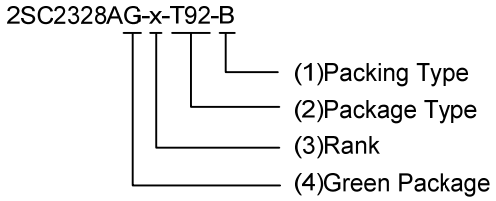
■ FEATURES

* Collector Dissipation Pc=1 W
* 3 W Output Application
* Complement of 2SA928A

■ ORDERING INFORMATION

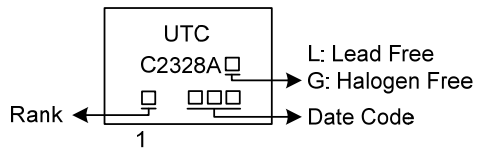
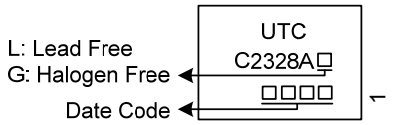
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC2328AL-x-T92-B	2SC2328AG-x-T92-B	TO-92	E	C	B	Tape Box
2SC2328AL-x-T92-K	2SC2328AG-x-T92-K	TO-92	E	C	B	Bulk
2SC2328AL-x-T9N-K	2SC2328AG-x-T9N-K	TO-92NL	E	C	B	Bulk
2SC2328AL-x-T9N-B	2SC2328AG-x-T9N-B	TO-92NL	E	C	B	Tape Box

Note: Pin Assignment: E: Emitter C: Collector B: Base



(1) B: Tape Box, K: Bulk
(2) T92: TO-92, T9N: TO-92NL
(3) x: refer to Classification of h_{FE}
(4) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

TO-92	TO-92NL
	

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	30	V
Collector-Emitter Voltage		V_{CEO}	30	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Dissipation	TO-92	P_C	500	mW
	TO-92NL		625	
Collector Current		I_C	2	A
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA, I_E=0	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=10mA, I_B=0	30			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA,I_C=0	5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V, I_E=0			100	nA
Emitter Cut-Off Current	I_{EBO}	V_{BE}=5V, I_C=0			100	nA
DC Current Gain (Note)	h_{FE}	V_{CE}=2V, I_C=500mA	100		320	
Base-Emitter On Voltage	$V_{BE(ON)}$	V_{CE}=2V, I_C=500mA			1	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=1.5A, I_B=0.03A			2	V
Output Capacitace	C_{OB}	V_{CB} =10V, I_E =0, f=1MHz		30		pF
Current Gain Bandwidth Product	f_T	V_{CE}=2V, I_C=500mA		120		MHz

■ CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	100-200	160-320